



FIG. 1

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A cross-sectional diagram of a device structure. The base is a thick black layer labeled "Gallium Nitride". On top of this base, there are several layers and features. From left to right: a thin white layer labeled "Metal 2 (Schottky)" with a thickness of 30; a white layer labeled "Aluminum Nitride" with a thickness of 50; a thin white layer labeled "Metal 1 (ohmic)" with a thickness of 30; a white layer labeled "Aluminum Nitride" with a thickness of 60; a thin white layer labeled "Metal 1 (ohmic)" with a thickness of 45; and a thin white layer labeled "Metal 2 (Schottky)" with a thickness of 30. A label "Area where surface electric breakdown is prevented" points to the black Gallium Nitride base. The numbers 30, 50, 60, 45, and 30 are written above their respective layers, indicating thicknesses.

FIG. 2